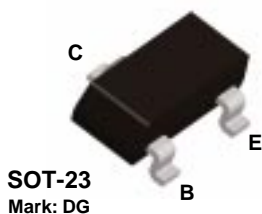


BCW68G



PNP General Purpose Amplifier

This device is designed for general purpose amplifier and switching applications at currents to 500 mA. Sourced from Process 63.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	45	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	800	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		*BCW68C	
P _D	Total Device Dissipation Derate above 25°C	350	mW
		2.8	mW/°C
R _{θJA}	Thermal Resistance, Junction to Ambient	357	°C/W

*Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

PNP General Purpose Amplifier

(continued)

BCW68G

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$		45	V
$V_{(BR)CES}$	Collector-Base Breakdown Voltage	$I_C = 10 \text{ } \mu\text{A}$		60	V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \text{ } \mu\text{A}, I_E = 0$		60	V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \text{ } \mu\text{A}, I_C = 0$		5.0	V
I_{CES}	Collector-Cutoff Current	$V_{CE} = 45 \text{ V}$ $V_{CE} = 45 \text{ V}, T_A = 150 \text{ }^\circ\text{C}$		20 10	nA μA
I_{EBO}	Emitter-Cutoff Current	$V_{EB} = 4.0 \text{ V}$		20	nA

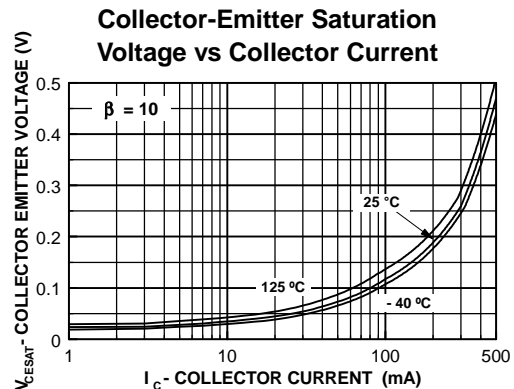
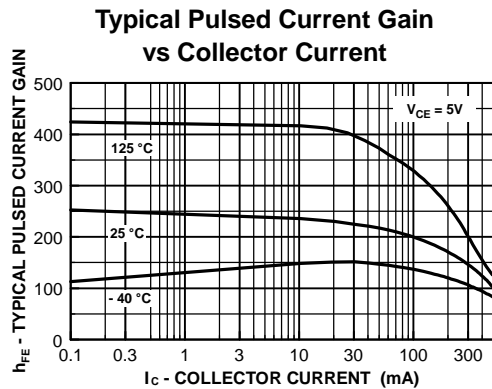
ON CHARACTERISTICS

h_{FE}	DC Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 300 \text{ mA}, V_{CE} = 1.0 \text{ V}$	120 160 60	400	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$		1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		2.0	V

SMALL SIGNAL CHARACTERISTICS

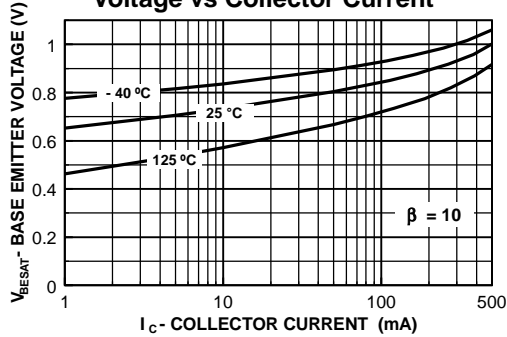
f_T	Current Gain - Bandwidth Product	$I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$	100		MHz
C_{obo}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		18	pF
C_{ibo}	Input Capacitance	$V_{EB} = 0.5 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		105	pF
NF	Noise Figure	$I_C = 0.2 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $R_S = 1.0 \text{ k}\Omega, f = 1.0 \text{ kHz},$ $B_W = 200 \text{ Hz}$		10	dB

Typical Characteristics

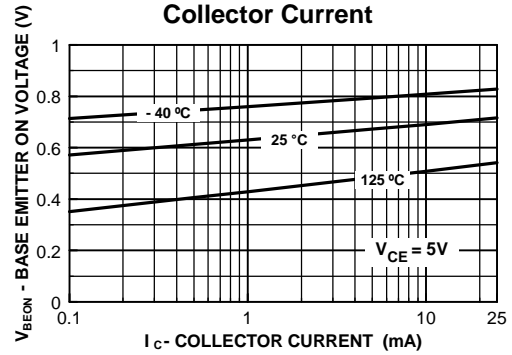


Typical Characteristics (continued)

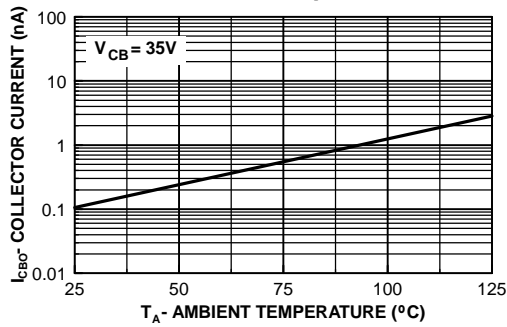
Base-Emitter Saturation Voltage vs Collector Current



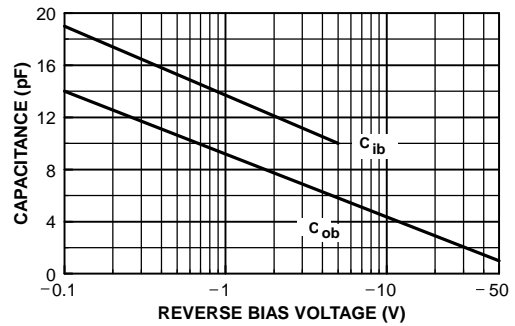
Base Emitter ON Voltage vs Collector Current



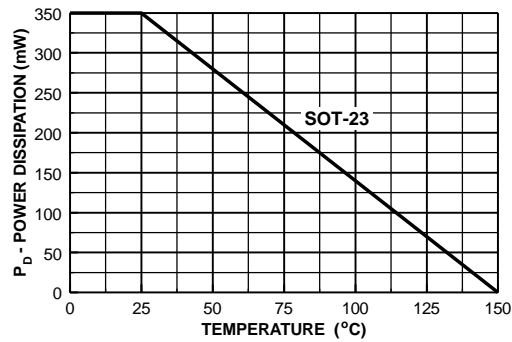
Collector-Cutoff Current vs. Ambient Temperature



Input and Output Capacitance vs Reverse Bias Voltage



Power Dissipation vs Ambient Temperature



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PRODUCT STATUS DEFINITIONS

Definition of Terms

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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